the specification of which is attached hereto

DECLARATION AND POWER OF ATTORNEY

As a below named inventor, I hereby declare that:

My residence, post office address, and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter claimed and for which a patent is sought on the invention entitled:

THYISTOR-BASED SRAM AND METHOD USING QUASI-PLANAR FINFET PROCESS FOR THE FABRICATION THEREOF

was filed on a	as Application Ser	rial No a	nd was amended	l on (i:	f applicable).	
hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above.						
do not know and damerica before this in the same was not in porior to this application to be material to section 1.56.	nvention thereof oublic use or on so ion. I acknowledg	or more than ale in the U ge the duty	n one year prior to nited States of A to disclose infor	to this app merica mo mation wl	lication, and that ore than one year hich is known to	
hereby claim foreig or Section 365(b) of 865(a) of any PCT in the United States, li- patent or inventor's priority is claimed:	any foreign appli nternational applic sted below and h	cation(s) for cation which ave also id	r patent or inven designated at le entified below a	tor's certife east one co any foreign	ficate, or Section cuntry other than n application for	
Prior Foreign Appli	cation(s):	,	-			
Number	Country	Day/Mon	th/Year filed	Priority (Yes	Claimed No	
hereby claim the benefit under 35 USC 119(e) of any United States provisional application(s) listed below:						
Prior Provisional A	pplication(s):		· ,			
Application Number Filing Date						
hereby claim the benefit under Title 35, United States Code, Section 120 of any United States application(s), or Section 365(c) of any PCT international application designating the						

the national or PCT international filing date of this application:

United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT international application in the manner provided by the first paragraph of Title 35, United States Code, Section 112, I acknowledge the duty to disclose material information as defined in Title 37, Code of Federal Regulations, Section 1.56 which occurred between the filing date of the prior application and

Prior U.S. Application(s):

Serial No.

Filing Date

Status: Patented, Pending, Abandoned

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

I hereby revoke any previous Powers of Attorney and appoint the following attorney(s) and/or agent(s), each said individual being a member or associate of The Law Offices of Mikio Ishimaru or being employed by Chartered Semiconductor Manufacturing Ltd.:

Mikio Ishimaru

Reg. No. 27,449

William D. Zahrt, II

Reg. No. 26,070

for so long as they remain with such law offices or company with full power of substitution and revocation, to prosecute this application and to transact in connection therewith all business in the Patent and Trademark Office and before competent International Authorities; said appointment to be to the exclusion of myself and my other attorney(s); and all future correspondence should be addressed to:

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